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Team Nexperia



60 V, 3 A PNP high power bipolar transistor 13 January 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60603NY.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Load switch

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- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

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T. I. I. A

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-3	А
I _{CM}	peak collector current	$t_p \le 1 \text{ ms}; \text{ pulsed}$	-	-	-8	А
R _{CEsat}	collector-emitter saturation resistance	I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	80	120	mΩ





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	C .
2	E	emitter	ل : !]	в-
3	E	emitter	q	۲×۲
4	В	base	មុច្ចប្	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PHPT60603PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT60603PY	0603PAB

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8. Limiting values

Table 5. Limiting values

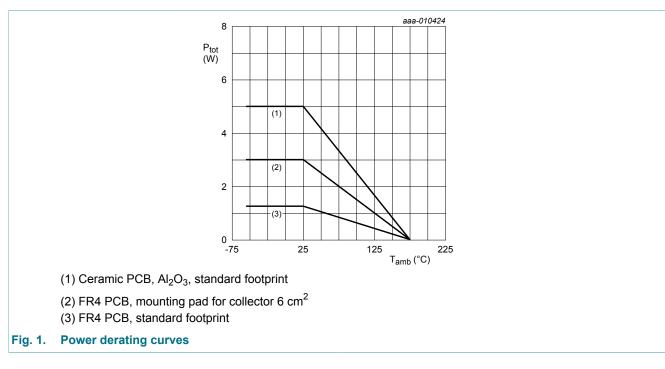
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-3	А
I _{CM}	peak collector current	$t_p \le 1 ms$; pulsed		-	-8	А
I _B	base current			-	-0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [4] Power dissipation from junction to mounting base.



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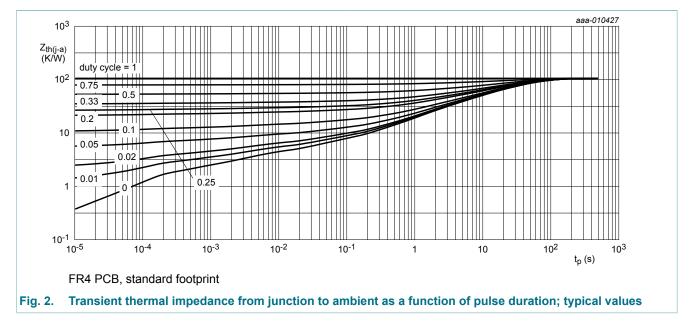
9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	50	K/W
			[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

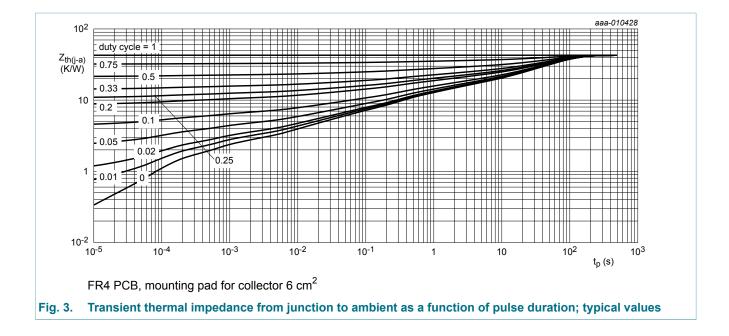




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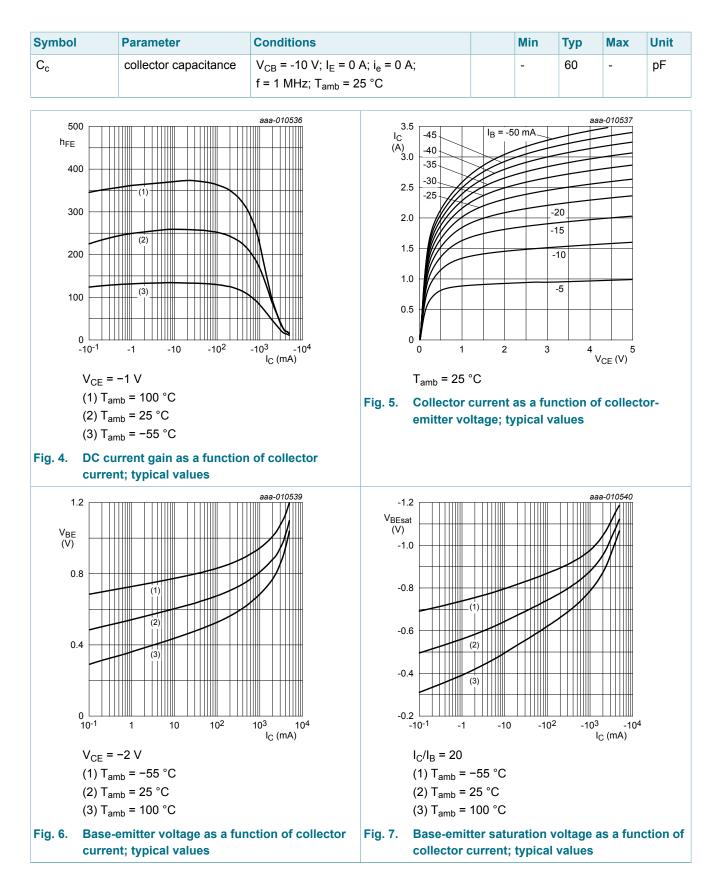
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -8 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_C = -500 mA; T_{amb} = 25 °C	150	250	-	
		$\begin{split} &V_{CE} \texttt{=-2 V; } I_{C} \texttt{=-1 A; } t_{p} \texttt{\leq} 300 \ \texttt{\mu}\texttt{s}; \\ &\bar{\delta} \texttt{\leq} 0.02 \text{ ; } T_{amb} \texttt{=} 25 \ ^{\circ}\text{C}\text{; pulsed} \end{split}$	150	225	-	
		V_{CE} = -2 V; I _C = -2 A; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C; pulsed	80	130	-	
		V_{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	35	75	-	
0 EGU	collector-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-100	-225	mV
		I_C = -3 A; I_B = -300 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	-	-240	-360	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	100	225	mΩ
		I_{C} = -3 A; I_{B} = -300 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	80	120	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-0.89	-1	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-1.02	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -0.1 A; T _{amb} = 25 °C	-	-0.83	-0.9	V
t _d	delay time	V_{CC} = -12.5 V; I_{C} = -1 A; I_{Bon} = -50 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = 50 mA; T _{amb} = 25 °C	-	85	-	ns
t _{on}	turn-on time		-	100	-	ns
t _s	storage time		-	350	-	ns
t _f	fall time		-	110	-	ns
t _{off}	turn-off time		-	460	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	110	-	MHz

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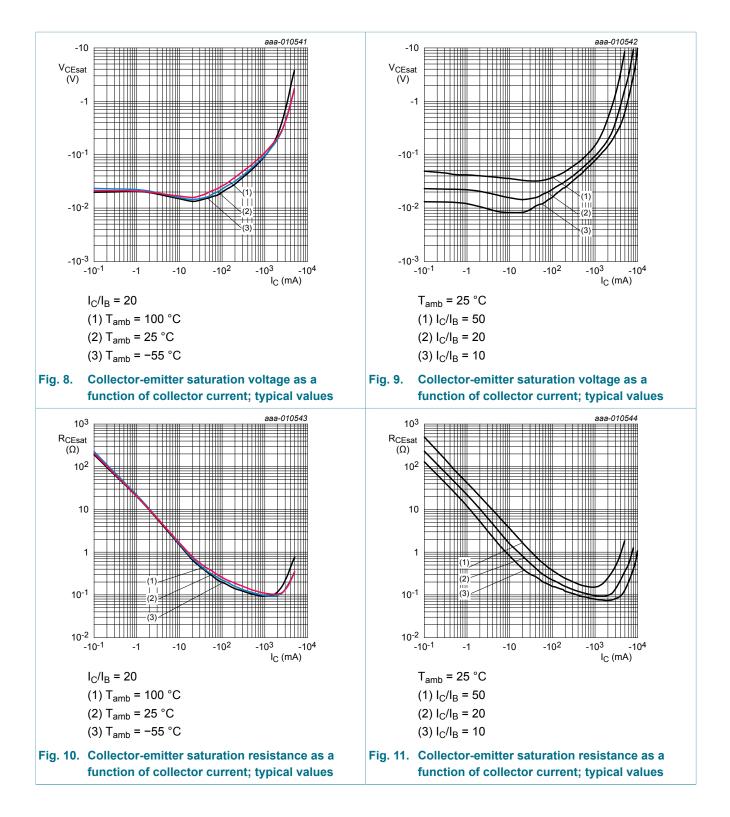
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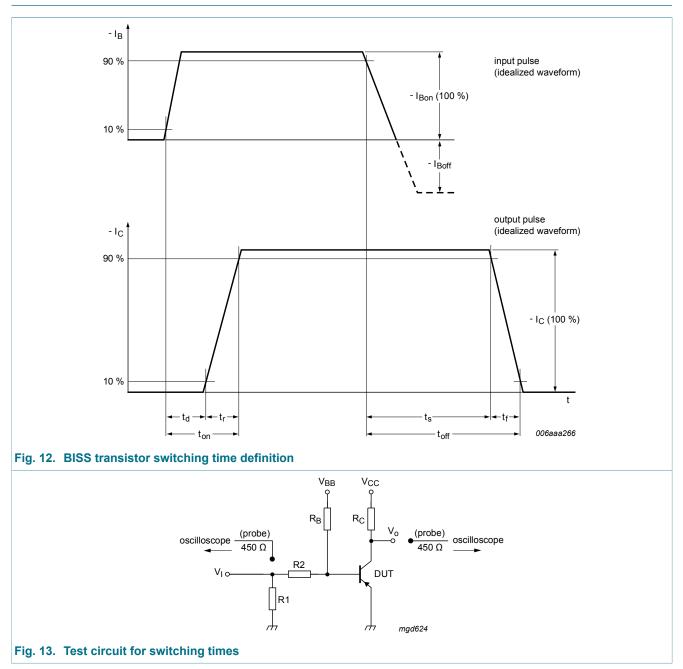
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11. Test information



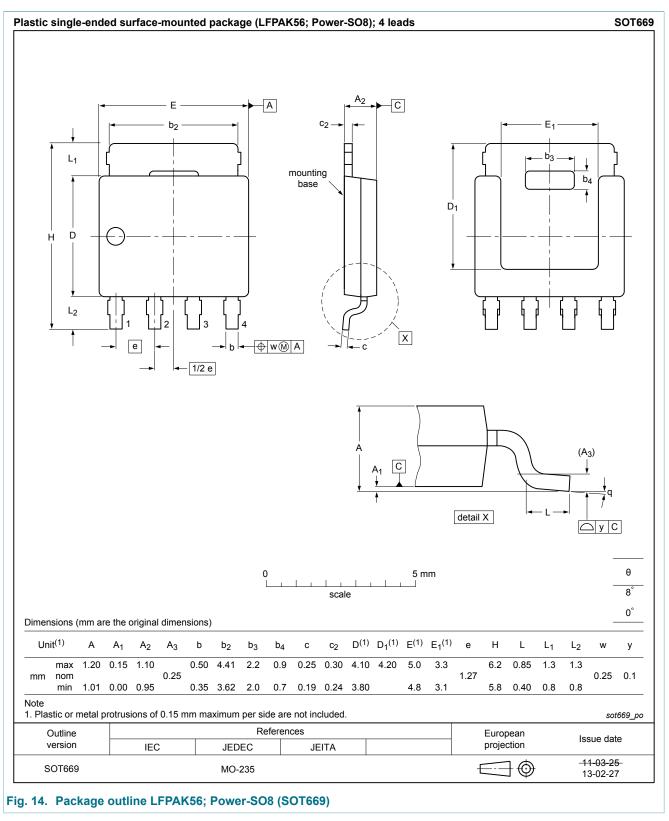
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



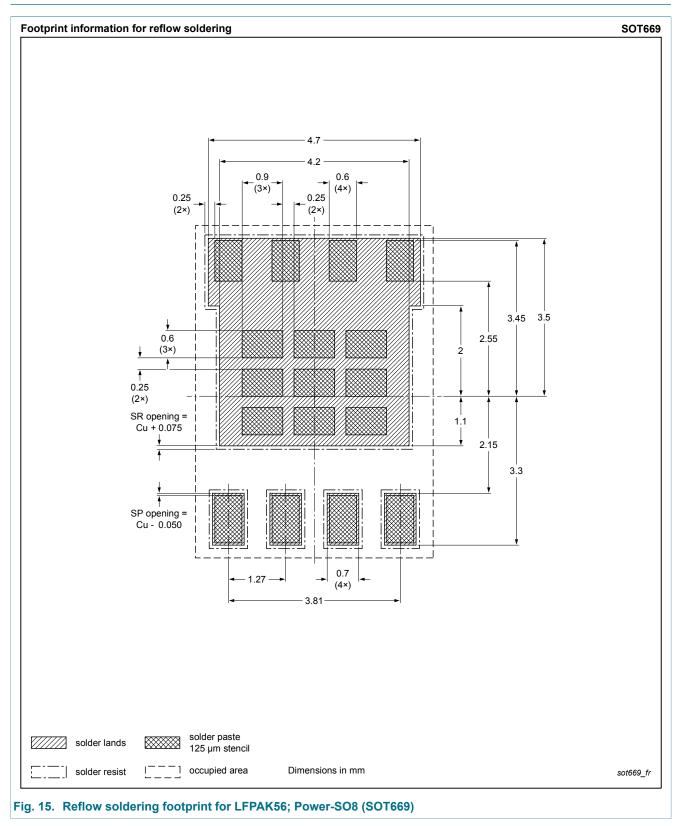
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Product data sheet

60 V, 3 A PNP high power bipolar transistor

13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT60603PY v.1	20140113	Product data sheet	-	-		

60 V, 3 A PNP high power bipolar transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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